

2SK1403A

Silicon N Channel MOS FET

REJ03G0943-0200

(Previous: ADE-208-1283)

Rev.2.00 Sep 07, 2005

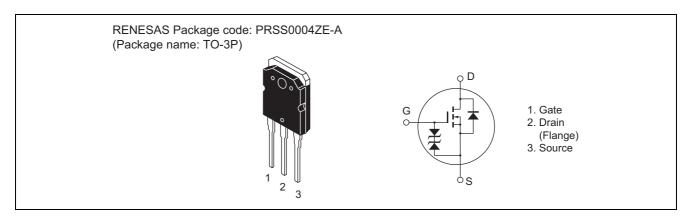
Application

High speed power switching

Features

- Low on-resistance
- High speed switching
- Low drive current
- No secondary breakdown
- Suitable for switching regulator and DC-DC converter

Outline



Absolute Maximum Ratings

 $(Ta = 25^{\circ}C)$

Item	Symbol	Ratings	Unit
Drain to source voltage	V _{DSS}	650	V
Gate to source voltage	V _{GSS}	±30	V
Drain current	I _D	8	Α
Drain peak current	I _{D(pulse)} *1	32	Α
Body to drain diode reverse drain current	I _{DR}	8	Α
Channel dissipation	Pch*2	100	W
Channel temperature	Tch	150	°C
Storage temperature	Tstg	-55 to +150	°C

Notes: 1. PW \leq 10 μ s, duty cycle \leq 1%

2. Value at $T_C = 25^{\circ}C$

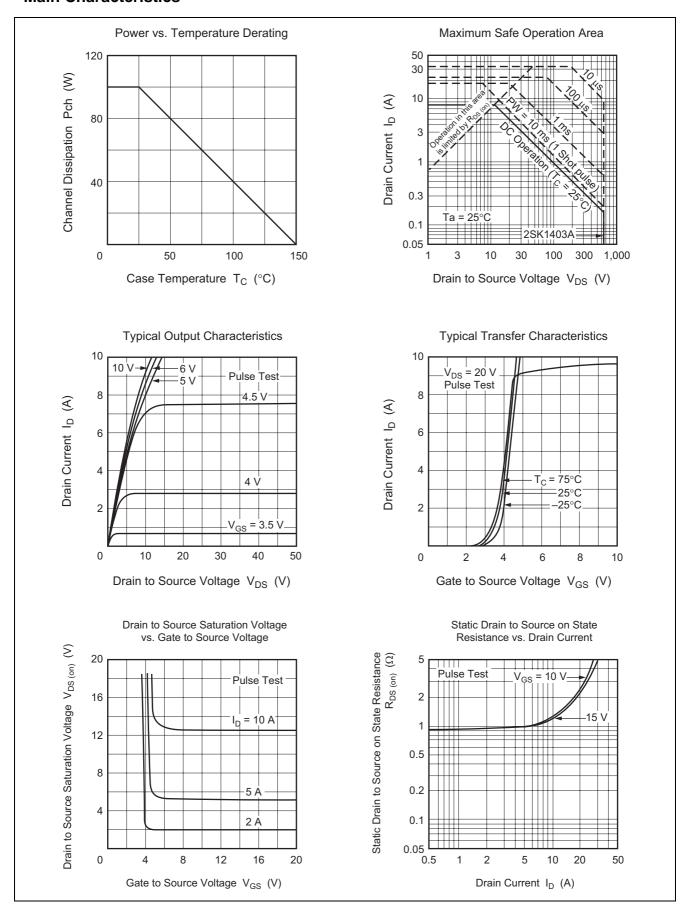
Electrical Characteristics

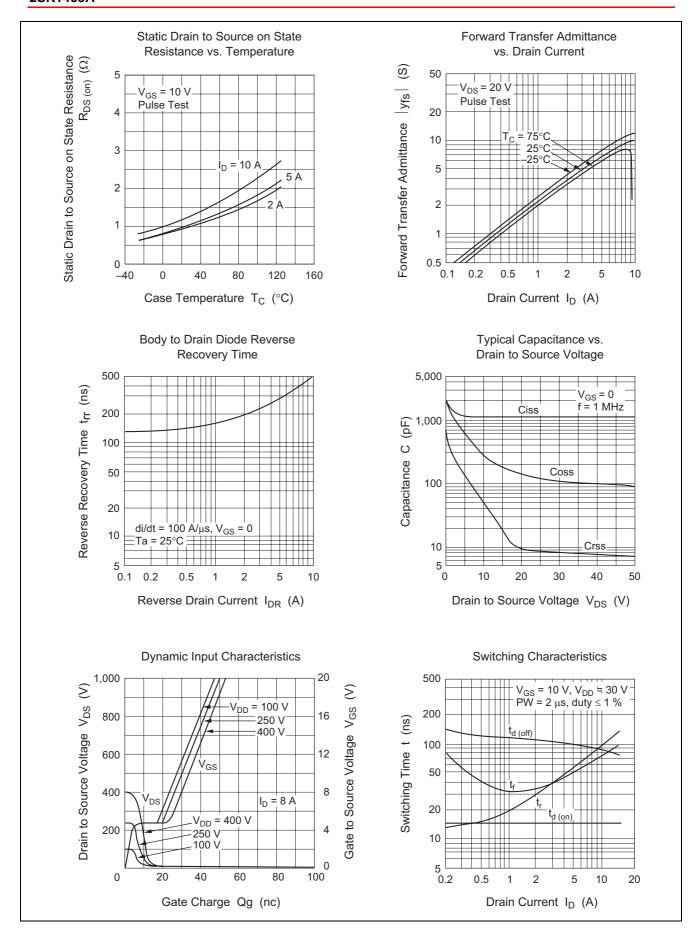
 $(Ta = 25^{\circ}C)$

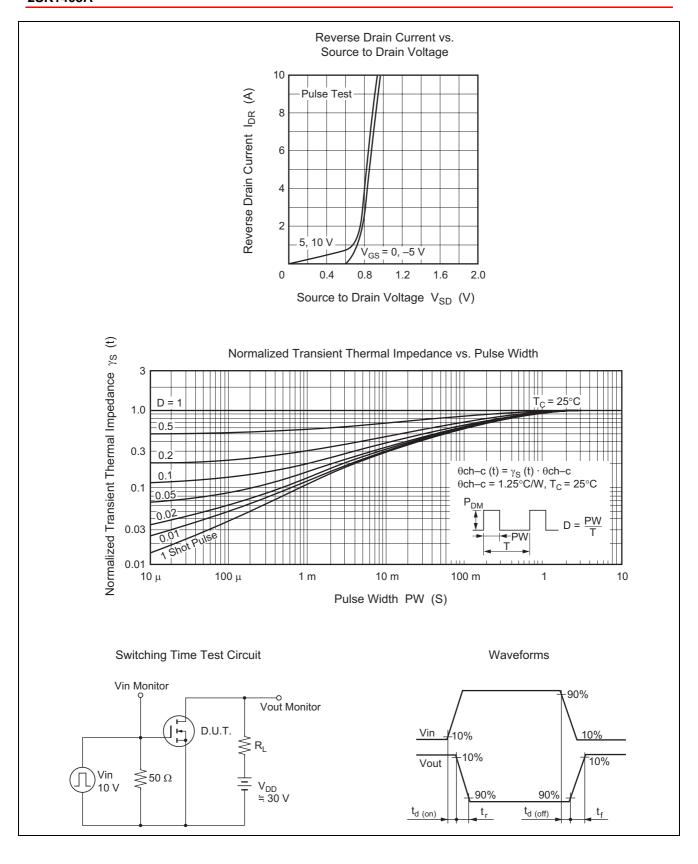
Item	Symbol	Min	Тур	Max	Unit	Test conditions	
Drain to source breakdown voltage	$V_{(BR)DSS}$	650	_	_	V	$I_D = 10 \text{ mA}, V_{GS} = 0$	
Gate to source breakdown voltage	V _{(BR)GSS}	±30	_	_	V	$I_G = \pm 100 \mu\text{A}, V_{DS} = 0$	
Gate to source leak current	I_{GSS}	_	_	±10	μΑ	$V_{GS} = \pm 25 \text{ V}, V_{DS} = 0$	
Zero gate voltage drain current	I _{DSS}	_	_	250	μΑ	$V_{DS} = 550 \text{ V}, V_{GS} = 0$	
Gate to source cutoff voltage	$V_{GS(off)}$	2.0	_	3.0	V	$I_D = 1 \text{ mA}, V_{DS} = 10 \text{ V}$	
Static drain to source on state	R _{DS(on)}	_	1.0	1.4	Ω	$I_D = 4 \text{ A}, V_{GS} = 10 \text{ V}^{*3}$	
resistance							
Forward transfer admittance	y _{fs}	4.0	6.5	_	S	$I_D = 4 A$, $V_{DS} = 10 V^{*3}$	
Input capacitance	Ciss	_	1180		pF	$V_{DS} = 10 \text{ V}, V_{GS} = 0,$	
Output capacitance	Coss	_	265	_	pF	f = 1 MHz	
Reverse transfer capacitance	Crss	_	50	_	pF	1	
Turn-on delay time	t _{d(on)}	_	15	_	ns	$I_D = 4 A$, $V_{GS} = 10 V$,	
Rise time	t _r	_	50	_	ns	$R_L = 7.5 \Omega$	
Turn-off delay time	$t_{d(off)}$	_	105	_	ns		
Fall time	t _f	_	45	_	ns		
Body to drain diode forward voltage	V_{DF}	_	0.95	_	V	$I_F = 8 A, V_{GS} = 0$	
Body to drain diode reverse recovery	t _{rr}	_	420	_	ns	$I_F = 8 A, V_{GS} = 0,$	
time						$di_F/dt = 100 A/\mu s$	

Note: 3. Pulse test

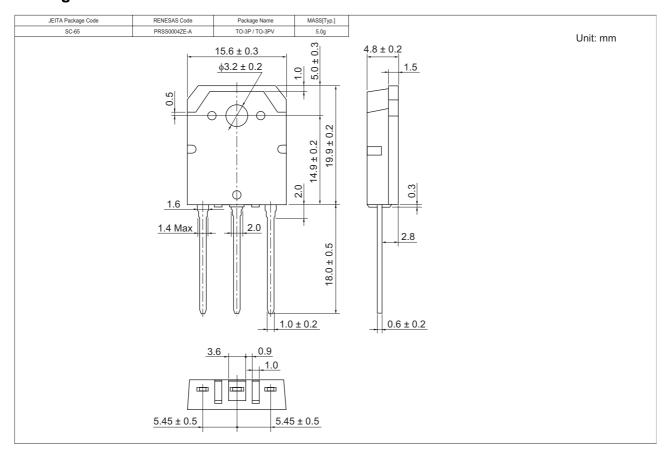
Main Characteristics







Package Dimensions



Ordering Information

Part Name	Quantity	Shipping Container
2SK1403A-E	360 pcs	Box (Tube)

Note: For some grades, production may be terminated. Please contact the Renesas sales office to check the state of production before ordering the product.

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